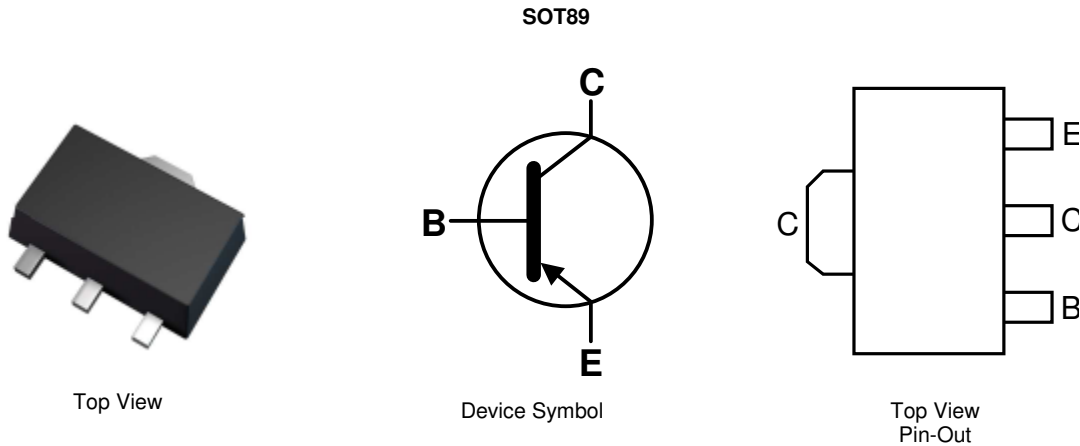


Features

- $BV_{CEO} > -50V$
- $I_C = -3A$ High Continuous Collector Current
- I_{CM} up to $-5A$ Peak Pulse Current
- 2W Power Dissipation
- Low Saturation Voltage $V_{CE(sat)} < -180mV @ 1A$
- $R_{CE(sat)} = 67m\Omega @ 2A$ for a Low Equivalent On-Resistance
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

Mechanical Data

- Case: SOT89
- Case Material: Molded Plastic, "Green" Molding Compound
UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish - Matte Tin Plated Leads, Solderable per
MIL-STD-202, Method 208 (3)
- Weight: 0.052 grams (Approximate)

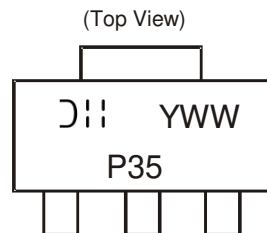


Ordering Information (Note 4)

Part Number	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
DPLS350Y-13	P35	13	12	2,500
DPLS350Y-13R	P35	13	12	4,000
DPLS350YTC	P35	13	12	4,000

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen and Antimony free, "Green" and Lead-Free.
 3. Halogen and Antimony free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information



P35 = Product Type Marking Code:
 YWW = Date Code Marking
 Y = Last Digit of Year ex: 5 = 2015
 WW = Week Code 01 - 53

Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-50	V
Collector-Emitter Voltage	V _{CEO}	-50	V
Emitter-Base Voltage	V _{EBO}	-6	V
Continuous Collector Current	I _C	-3	A
Peak Pulse Current	I _{CM}	-5	A
Base Current	I _B	-500	mA

Thermal Characteristics

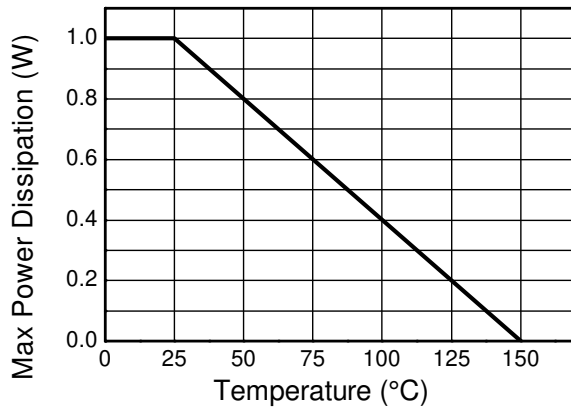
Characteristic	Symbol	Value	Unit
Power Dissipation	P _D	(Note 5)	1
		(Note 6)	1.6
		(Note 7)	2.0
Thermal Resistance, Junction to Ambient Air	R _{θJA}	(Note 5)	125
		(Note 6)	78
		(Note 7)	62.5
Thermal Resistance, Junction to Lead	R _{θJL}	5.7	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

ESD Ratings (Note 9)

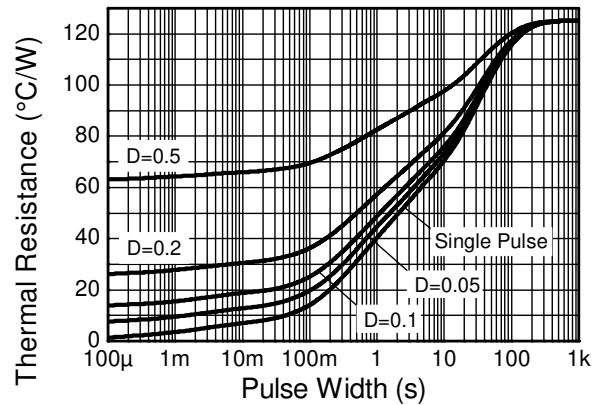
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	C

- Notes:
5. For a device mounted with the exposed collector pad on 15mm x 15mm 1oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
 6. Same as note (5), except the device is mounted on 25mm x 25mm 1oz copper.
 7. Same as note (5), except the device is mounted on 50mm x 50mm 1oz copper.
 8. Thermal resistance from junction to solder-point (on the exposed collector pad).
 9. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

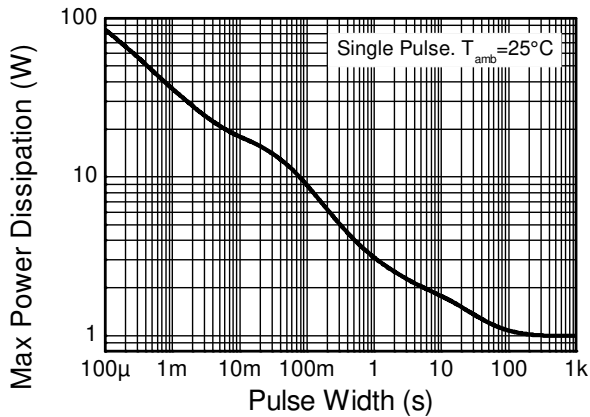
Thermal Characteristics and Derating Information



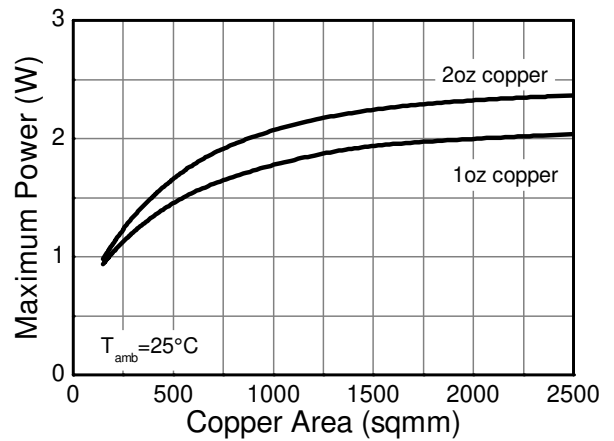
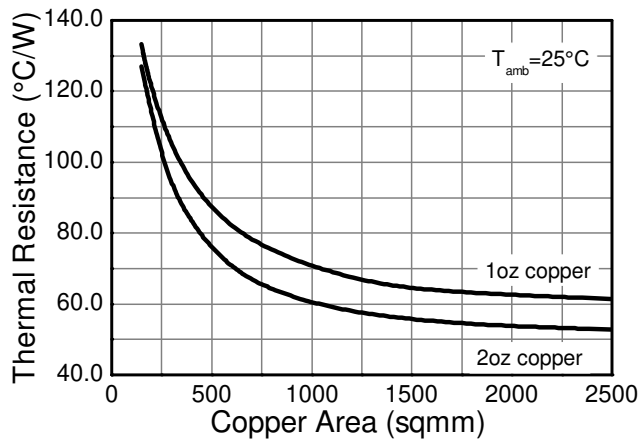
Derating Curve



Transient Thermal Impedance



Pulse Power Dissipation



Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	-50	—	—	V	I _C = -100μA
Collector-Emitter Breakdown Voltage (Note 10)	BV _{CEO}	-50	—	—	V	I _C = -10mA
Emitter-Base Breakdown Voltage	BV _{EBO}	-6	—	—	V	I _E = -100μA
Collector-Emitter Cut-off Current	I _{CES}	—	—	-100	nA	V _{CE} = -50V
Collector Cut-off Current	I _{CBO}	—	—	-100	nA	V _{CB} = -50V
				-50	μA	V _{CB} = -50V, T _A = +150°C
Emitter Cut-off Current	I _{EBO}	—	—	-100	nA	V _{EB} = -5V
Static Forward Current Transfer Ratio (Note 10)	h _{FE}	200	—	—	—	I _C = -100mA, V _{CE} = -2V
		200		—		I _C = -500mA, V _{CE} = -2V
		200		450		I _C = -1A, V _{CE} = -2V
		130		—		I _C = -2A, V _{CE} = -2V
		80		—		I _C = -3A, V _{CE} = -2V
Collector-Emitter Saturation Voltage (Note 10)	V _{CE(sat)}	—	—	-90	mV	I _C = -500mA, I _B = -50mA
				-180		I _C = -1A, I _B = -50mA
				-320		I _C = -2A, I _B = -100mA
				-270		I _C = -2A, I _B = -200mA
				-390		I _C = -3A, I _B = -300mA
Equivalent On-Resistance	R _{CE(sat)}	—	67	135	mΩ	I _C = -2A, I _B = -200mA
Base-Emitter Saturation Voltage (Note 10)	V _{BE(sat)}	—	—	-1.1	V	I _C = -2A, I _B = -100mA
				-1.2		I _C = -3A, I _B = -300mA
Base-Emitter Turn-On Current (Note 10)	V _{BE(on)}	—	—	-1.1	V	I _C = -1A, V _{CE} = -2V
Transition Frequency	f _T	100	—	—	MHz	I _C = -100mA, V _{CE} = -5V, f = 100MHz
Collector Output Capacitance	C _{obo}	—	—	35	pF	V _{CB} = -10V, I _E = 0, f = 1MHz
Turn-On Time	t _(ON)	—	87	—	ns	V _{CC} = -30v, I _{CC} = 150mA I _{B1} = - I _{B2} = 15mA
Delay Time	t _D	—	41	—	ns	
Rise Time	t _R	—	46	—	ns	
Turn-Off Time	t _(OFF)	—	294	—	ns	
Storage Time	t _S	—	250	—	ns	
Fall Time	t _F	—	44	—	ns	

Note: 10. Measured under pulsed conditions. Pulse width ≤ 300μs. Duty cycle ≤ 2%.

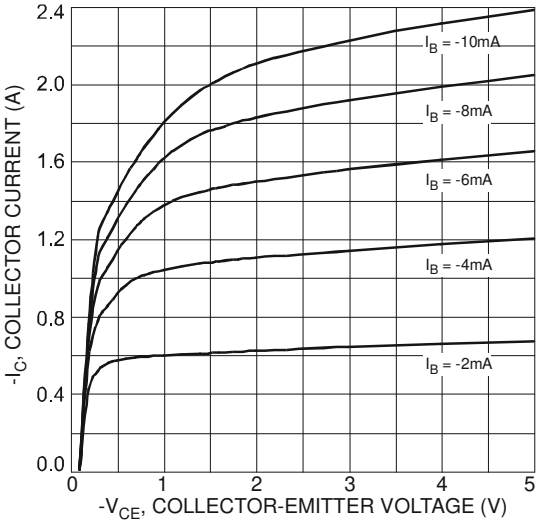


Figure 1 Typical Collector Current vs. Collector-Emitter Voltage

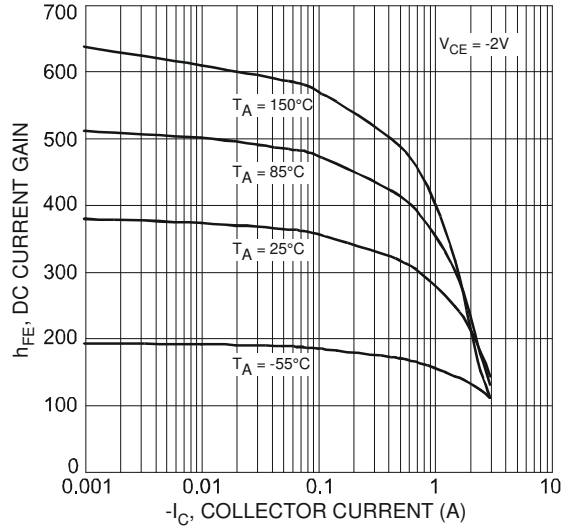


Figure 2 Typical DC Current Gain vs. Collector Current

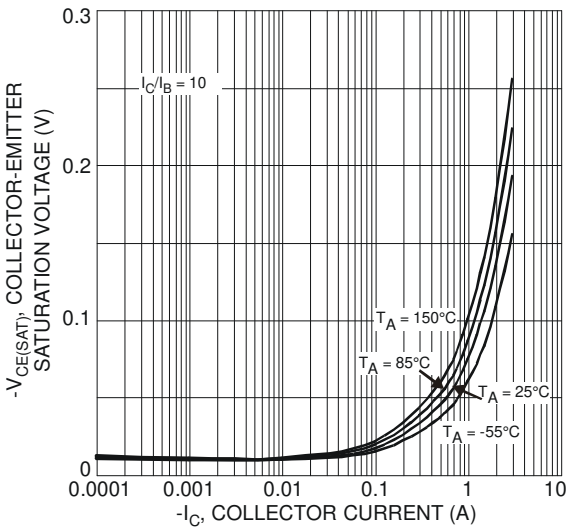


Figure 3 Typical Collector-Emitter Saturation Voltage vs. Collector Current

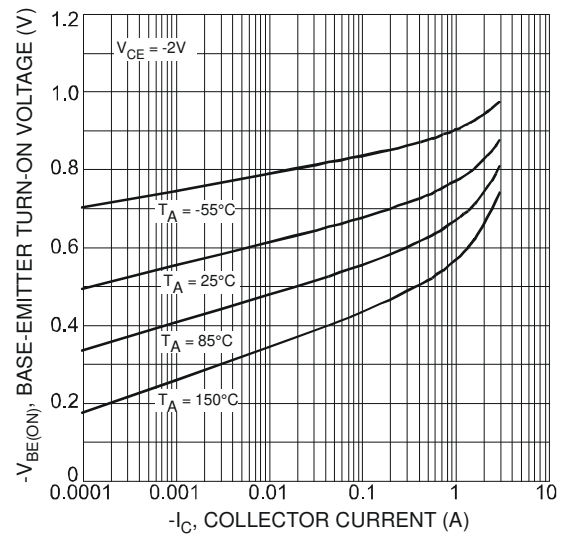


Figure 4 Typical Base-Emitter Turn-On Voltage vs. Collector Current

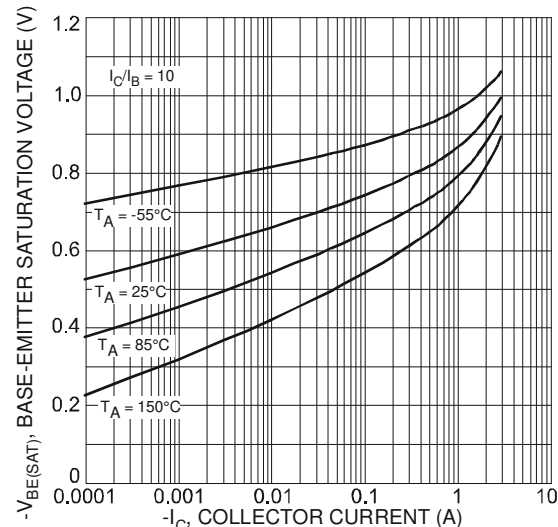


Figure 5 Typical Base-Emitter Saturation Voltage vs. Collector Current

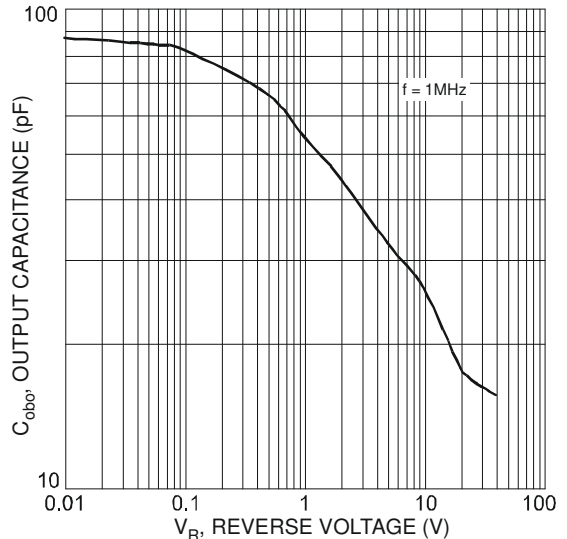


Figure 6 Typical Output Capacitance Characteristics

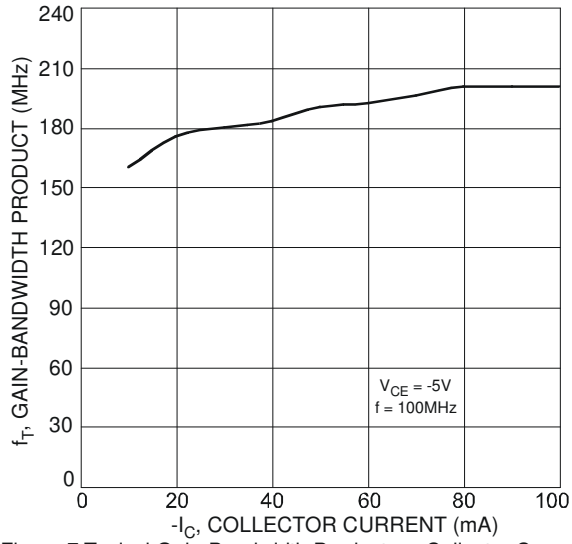
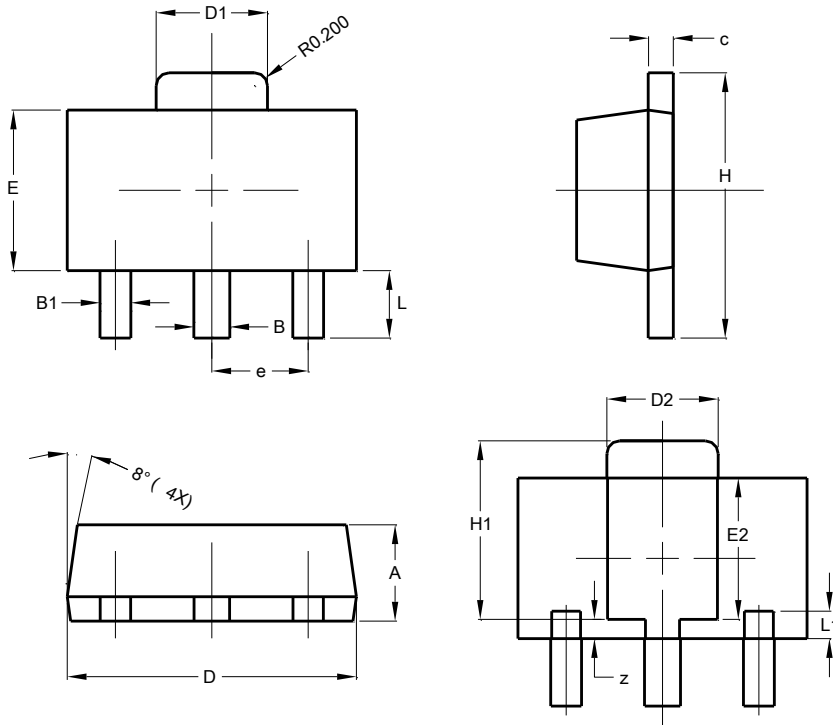


Figure 7 Typical Gain-Bandwidth Product vs. Collector Current

Package Outline Dimensions

Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.

SOT89

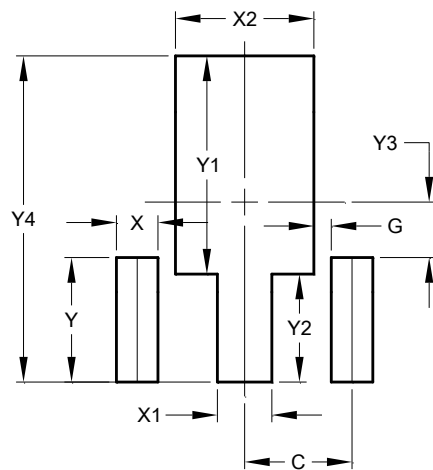


SOT89			
Dim	Min	Max	Typ
A	1.40	1.60	1.50
B	0.50	0.62	0.56
B1	0.42	0.54	0.48
c	0.35	0.43	0.38
D	4.40	4.60	4.50
D1	1.62	1.83	1.733
D2	1.61	1.81	1.71
E	2.40	2.60	2.50
E2	2.05	2.35	2.20
e	-	-	1.50
H	3.95	4.25	4.10
H1	2.63	2.93	2.78
L	0.90	1.20	1.05
L1	0.327	0.527	0.427
z	0.20	0.40	0.30
All Dimensions in mm			

Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.

SOT89



Dimensions	Value (in mm)
C	1.500
G	0.244
X	0.580
X1	0.760
X2	1.933
Y	1.730
Y1	3.030
Y2	1.500
Y3	0.770
Y4	4.530

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